TECHNICAL DATA
DATA SHEET 1177, REV. B

THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY

DESCRIPTION: A 50/100/150 VOLT, 15 AMP, 40 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

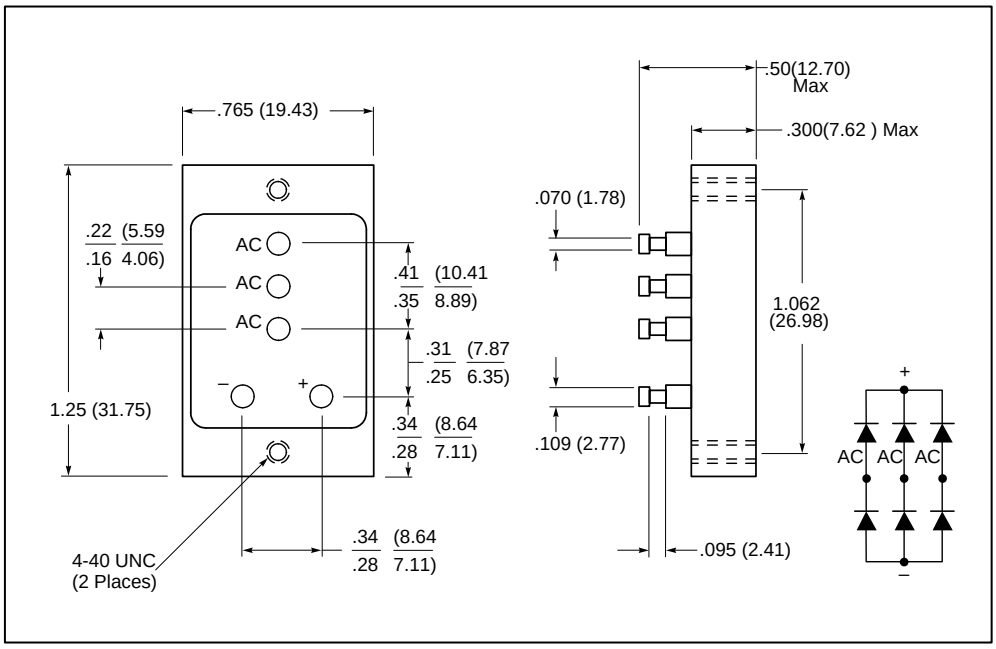
MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^oC$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) S10A305HE S10A310HE S10A315HE	-	-	-	 50 100 150	Vdc
Average DC Output Current (T_C = Case Temp) (I_o)	$T_C = 55^oC$ $T_C = 100^oC$ $T_C = 125^oC$	-	-	15 9.0 5.0	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^oC$ $T_A = 55^oc$ $T_A = 100^oc$	-	-	4.75 3.75 2.25	Amps
Peak Single Cycle Surge Current (I_{FSM})	t_p = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	100	Amps(pk)
Peak Recurring Surge Current (I_{FRM})	$T_A = 25^oC$	-	-	35	Amps
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	°C
Maximum Forward Voltage (V_f)	I_f = 6.0A (300 µsec pulse, duty cycle < 2%)	-	-	1.0	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25°$ C $T_A = 100°$ C	-	-	10 100	µAmps
Reverse Recovery Time (t_{rr})	I_f = 0.5A, I_r = 1.0A, I_{rr} = 0.25A	-	-	40	nsec
Thermal Resistance (θ_{JL})	-	-	-	3.0	°C/W

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MECHANICAL DIMENSIONS: In Inches / mm



Notes:
Case finish - Black Anodized
Potted dimension - uncontrolled

FIG. 410

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